

## Linear Systems Low Leakage Low Noise JFET

The LS846 is a high-performance JFET featuring extremely low noise and low leakage and is targeted for use in a wide range of precision instrumentation applications.

The 6 Pin SOT-23 package provides ease of manufacturing, and a lower cost assembly option.

(See Packaging Information).

### LS846 Applications:

- Wideband Differential Amps
- High-Speed, Temp-Compensated Single-Ended Input Amps
- High-Speed Comparators
- Impedance Converters and vibrations detectors.

### FEATURES

LOW LEAKAGE	$I_G = 15\text{pA TYP.}$
LOW NOISE	$e_n = 3\text{nV}/\sqrt{\text{Hz}} \text{ TYP.}$

### ABSOLUTE MAXIMUM RATINGS @ 25°C (unless otherwise noted)

#### Maximum Temperatures

Storage Temperature	-65°C to +150°C
Operating Junction Temperature	+135°C

#### Maximum Voltage and Current– Note 1

$-V_{GSS}$	Gate Voltage to Drain or Source	60V
$-V_{GDS}$	Gate Voltage to Drain or Source	60V
$-V_{DSO}$	Drain to Source Voltage	60V
$-I_{G(f)}$	Gate Forward Current	50mA

#### Maximum Power Dissipation

Device Dissipation @ Free Air – Total	350mW @ +125°C
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### ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTICS	MIN.	TYP.	MAX.	UNITS	CONDITIONS
$BV_{GSS}$	Breakdown Voltage	60	--	--	V	$V_{DS} = 0$ $I_D = 1\text{nA}$
<b>TRANSCONDUCTANCE</b>						
$Y_{fss}$	Full Conduction	1500	--	--	$\mu\text{mho}$	$V_{DG} = 15\text{V}$ $V_{GS} = 0\text{V}$ $f = 1\text{kHz}$
$Y_{fs}$	Typical Operation	1000	1500	--	$\mu\text{mho}$	$V_{DG} = 15\text{V}$ $I_D = 500\mu\text{A}$
<b>DRAIN CURRENT</b>						
$I_{DSS}$	Full Conduction	1.5	5	15	mA	$V_{DG} = 15\text{V}$ $V_{GS} = 0\text{V}$
<b>GATE VOLTAGE</b>						
$V_{GS(off)}$ or $V_p$	Pinchoff voltage	1	--	3.5	V	$V_{DS} = 15\text{V}$ $I_D = 1\text{nA}$
$V_{GS(on)}$	Operating Range	0.5	--	3.5	V	$V_{DS} = 15\text{V}$ $I_D = 500\mu\text{A}$
<b>GATE CURRENT</b>						
$-I_{Gmax.}$	Operating	--	15	50	pA	$V_{DG} = 15\text{V}$ $I_D = 500\mu\text{A}$
$-I_{Gmax.}$	High Temperature	--	--	50	nA	$T_A = +125^\circ\text{C}$
$-I_{Gmax.}$	Reduced $V_{DG}$	--	5	30	pA	$V_{DG} = 3\text{V}$ $I_D = 500\mu\text{A}$
$-I_{GSSmax.}$	At Full Conduction	--	--	100	pA	$V_{DG} = 15\text{V}$ $V_{DS} = 0$
<b>OUTPUT CONDUCTANCE</b>						
$Y_{OSS}$	Full Conduction	--	--	20	$\mu\text{mho}$	$V_{DG} = 15\text{V}$ $V_{GS} = 0\text{V}$
$Y_{OS}$	Operating	--	0.2	2	$\mu\text{mho}$	$V_{DG} = 15\text{V}$ $I_D = 500\mu\text{A}$
<b>NOISE</b>						
NF	Figure	--	--	0.5	dB	$V_{DS} = 15\text{V}$ $V_{GS} = 0\text{V}$ $R_G = 10\text{M}\Omega$ $f = 100\text{Hz}$ $\text{NBW} = 6\text{Hz}$
$e_n$	Noise Voltage	--	3	7	nV/ $\sqrt{\text{Hz}}$	$V_{DS} = 15\text{V}$ $I_D = 500\mu\text{A}$ $f = 1\text{kHz}$ $\text{NBW} = 1\text{Hz}$
<b>CAPACITANCE</b>						
$C_{iss}$	Input	--	--	8	pF	$V_{DS} = 15\text{V}$ $I_D = 500\mu\text{A}$
$C_{rss}$	Reverse Transfer	--	--	3		$V_{DG} = 15\text{V}$ $I_D = 500\mu\text{A}$

Note 1 – These ratings are limiting values above which the serviceability of any semiconductor may be impaired

### Available Packages:

LS846 / LS846 in SOT-23  
LS846 / LS846 available as bare die  
Please contact [Micross](http://www.micross.com) for full package and die dimensions

